CPW4-1200S020B–Silicon Carbide Schottky Diode Chip

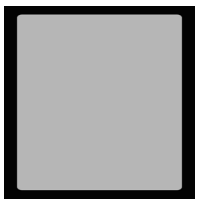
Z-Rec™ Rectifier

V_{RRM} = 1200 V
$I_{F(AVG)}$ = 20 A
Q_c = 130 nC

Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Swtitching
- Positive Temperature Coefficient on V_F

Chip Outline



Part Number	Anode	Cathode	Package	Marking
CPW4-1200S020B	Al	Ni/Ag	Sawn on Foil	Wafer # on Foil

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_{DC}	DC Blocking Voltage	1200	V		
$I_{F(AVG)}$	Average Forward Current	20	A	T_J=175°C	
I_{FRM}	Repetitive Peak Forward Surge Current	91	A	T_C=25°C, t_p=10 ms, Half Sine Wave	1
I_{FSM}	Non-Repetitive Peak Forward Surge Current	130	A	T_C=25°C, t_p=10 ms, Half Sine Wave	1
T_J , T_{stg}	Operating Junction and Storage Temperature	-55 to +175	°C		

Electrical Characteristics

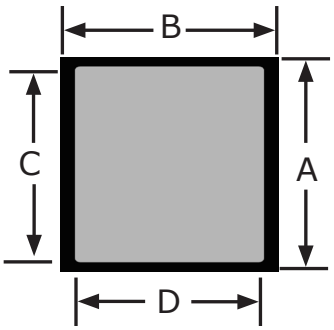
Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8 3	V	I_F = 20 A T_J=25°C I_F = 20 A T_J=175°C	
I_R	Reverse Current	35 65	200 400	µA	V_R = 1200 V T_J=25°C V_R = 1200 V T_J=175°C	
Q_C	Total Capacitive Charge	130		nC	V_R = 1200 V, I_F = 20 A di/dt = 200 A/µs T_J = 25°C	
C	Total Capacitance	1500 93 67		pF	V_R = 0 V, T_J = 25°C, f = 1 MHz V_R = 400 V, T_J = 25°C, f = 1 MHz V_R = 800 V, T_J = 25°C, f = 1 MHz	

Note:
1. Assumes θJC Thermal Resistance of 0.62°C/W or less

Mechanical Parameters

Parameter	Typ.	Unit
Die Size	3.08 x 3.08	mm
Anode Pad Size	2.79 x 2.79	mm
Anode Pad Opening	2.51 x 2.51	mm
Thickness	377 ± 10%	µm
Wafer Size	100	mm
Anode Metalization (Al)	4	µm
Cathode Metalization (Ni/Ag)	1.4	µm
Frontside Passivation	Polyimide	

Chip Dimensions



symbol	dimension	
	mm	inch
A	3.08	0.121
B	3.08	0.121
C	2.51	0.099
D	2.51	0.099

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The die-on-tape method of delivering these SiC die may be considered a means of temporary storage only. Due to an increase in adhesion over time, die stored for an extended period may affix too strongly to the tape. These die should be stored in a temperature-controlled nitrogen dry box soon after receipt. Cree will further recommend that all die be removed from tape to a waffle pack, to a similar storage medium, or used in production within 2 – 3 weeks of delivery to assure 100% release of all die without issues.

Cree, Inc.
4600 Silicon Drive
Durham, NC 27703
USA Tel: +1.919.313.5300
Fax: +1.919.313.5451
www.cree.com/power